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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/015,847	12/10/2001	Theodore J. Letavic	US 010610	3619
24737	7590	11/18/2003	EXAMINER	
PHILIPS INTELLECTUAL PROPERTY & STANDARDS			LEWIS, MONICA	
P.O. BOX 3001			ART UNIT	PAPER NUMBER
BRIARCLIFF MANOR, NY 10510			2822	

DATE MAILED: 11/18/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)
	10/015,847	LETAVIC ET AL.
	Examiner Monica Lewis	Art Unit 2822

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) Responsive to communication(s) filed on 21 October 2003.
- 2a) This action is FINAL. 2b) This action is non-final.
- 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) Claim(s) 1-12 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) Claim(s) _____ is/are allowed.
- 6) Claim(s) 1-12 is/are rejected.
- 7) Claim(s) _____ is/are objected to.
- 8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) The specification is objected to by the Examiner.
- 10) The drawing(s) filed on 18 August 2003 is/are: a) accepted or b) objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. §§ 119 and 120

- 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- * See the attached detailed Office action for a list of the certified copies not received.
- 13) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application) since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.
a) The translation of the foreign language provisional application has been received.
- 14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121 since a specific reference was included in the first sentence of the specification or in an Application Data Sheet. 37 CFR 1.78.

Attachment(s)

- | | |
|--|--|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) Paper No(s). _____ . |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____ . | 6) <input type="checkbox"/> Other: _____ . |

DETAILED ACTION

1. This action is in response to the request for continued examination filed

October 21, 2003.

Specification

2. The amendment filed 8/18/03 is objected to under 35 U.S.C. 132 because it introduces new matter into the disclosure. 35 U.S.C. 132 states that no amendment shall introduce new matter into the disclosure of the invention. The added material in the amendment to the drawings does not appear to be supported by the original disclosure (For Example: See Page 6 Lines 13-16 and Page 7 Lines 1 and 2). The amendment appears to contradict what is disclosed in the original disclosure.

Applicant is required to cancel the new matter in the reply to this Office Action.

Claim Rejections - 35 USC § 103

3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

4. Claims 1-5, 7-9 and 11 are rejected under 35 U.S.C. 103(a) as obvious over Merchant (U.S. Patent No. 5,412,241) in view of Applicant's Related Art.

In regards to claim 1, Merchant discloses the following:

a) a buried oxide layer (2) formed over a semiconductor substrate (3) (For Example: See Figure 1);

b) a silicon layer (1) formed over the buried oxide layer (For Example: See Figure 1);

c) a top oxide layer (6) formed over the silicon layer (For Example: See Figure 1); and

d) a first gate oxide (8) formed over the silicon layer adjacent the top oxide layer (For Example: See Figure 1).

In regards to claim 1, Merchant fails to disclose the following:

a) a second gate oxide formed over a portion of the first gate oxide.

However, Applicant's Related Art discloses a second gate oxide over a portion of the first gate oxide (For Example: See Figure 2). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a second gate oxide as disclosed in Applicant's Related Art because it aids in increasing the breakdown voltage (For Example: See Page 6 Lines 11 and 12).

Additionally, since Merchant and Applicant's Related Art are both from the same field of endeavor, the purpose disclosed by Applicant's Related Art would have been recognized in the pertinent art of Merchant.

In regards to claim 2, Merchant discloses the following:

a) the silicon layer comprises a source region (10), a body region (9), and a drift region (4) (For Example: See Figure 1).

In regards to claim 3, Merchant discloses the following:

a) the first gate oxide is formed over the drift region, the body region, and the source region (For Example: See Figure 1).

In regards to claim 4, Merchant discloses the following:

a) the first gate oxide, top oxide layer and the body region (For Example: See Figure 1).

In regards to claim 4, Merchant fails to disclose the following:

- a) a second gate oxide.

However, Applicant's Related Art discloses a second gate oxide (For Example: See Figure 2). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a second gate oxide as disclosed in Applicant's Related Art because it aids in increasing the breakdown voltage (For Example: See Page 6 Lines 11 and 12).

Additionally, since Merchant and Applicant's Related Art are both from the same field of endeavor, the purpose disclosed by Applicant's Related Art would have been recognized in the pertinent art of Merchant.

In regards to claims 5 and 9, Merchant discloses the following:

- a) a field plate (7) formed over the top oxide layer, the first gate oxide (For Example: See Figure 1).

In regards to claims 5 and 9, Merchant fails to disclose the following:

- a) a second gate oxide.

However, Applicant's Related Art discloses a second gate oxide (For Example: See Figure 2). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a second gate oxide as disclosed in Applicant's Related Art because it aids in increasing the breakdown voltage (For Example: See Page 6 Lines 11 and 12).

Additionally, since Merchant and Applicant's Related Art are both from the same field of endeavor, the purpose disclosed by Applicant's Related Art would have been recognized in the pertinent art of Merchant.

In regards to claims 7 and 11, Merchant fails to disclose the following:

- a) the first gate oxide has a length of approximately $3\text{-}4\mu\text{m}$, and wherein the second gate oxide has a length of approximately $1\text{-}2\mu\text{m}$.

However, the applicant has not established the critical nature of the dimension where the first gate oxide has a length of approximately $3\text{-}4\mu\text{m}$, and wherein the second gate oxide has a length of approximately $1\text{-}2\mu\text{m}$. “The law is replete with cases in which the difference between the claimed invention and the prior art is some range or other variable within the claims. . . . In such a situation, the applicant must show that the particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range.” *In re Woodruff*, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990).

In regards to claim 8, Merchant discloses the following:

- a) a buried oxide layer formed over a semiconductor substrate (For Example: See Figure 1);
- b) a silicon layer formed over the buried oxide layer, wherein the silicon layer comprises a source region, a body region, and a drift region (For Example: See Figure 1);
- c) a top oxide layer formed over the silicon layer (For Example: See Figure 1); and
- d) a first gate oxide formed over the silicon layer adjacent the top oxide layer (For Example: See Figure 1).

In regards to claim 8, Merchant discloses the following:

- a) the first gate oxide, top oxide layer and the body region (For Example: See Figure 1).

In regards to claim 8, Merchant fails to disclose the following:

- a) a second gate oxide.

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However, Applicant's Related Art discloses a second gate oxide (For Example: See Figure 2). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a second gate oxide as disclosed in Applicant's Related Art because it aids in increasing breakdown voltage.

Additionally, since Merchant and Applicant's Related Art are both from the same field of endeavor, the purpose disclosed by Applicant's Related Art would have been recognized in the pertinent art of Merchant (For Example: See Page 6 Lines 11 and 12).

5. Claims 6 and 10 are rejected under 35 U.S.C. 103(a) as obvious over Merchant (U.S. Patent No. 5,412,241) in view of Applicant's Related Art and Seeds et al. (U.S. Patent No. 3,936,858).

In regards to claims 6 and 10, Merchant discloses the following:

a) the first gate oxide has a thickness in a range of approximately 300-600A (For Example: See Column 2 Lines 39 and 40).

In regards to claims 6 and 10, Merchant fails to disclose the following:

a) a second gate oxide has a thickness in a range of approximately 900-1200A.

However, Seeds et al. ("Seeds") discloses a gate oxide that has a thickness around 1200A (For Example: See Column 8 Lines 52-55). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a gate oxide that has a thickness around 1200A as disclosed in Seeds because it aids in increasing the threshold voltage (For Example: See Column 8 Lines 52-55).

Additionally, the applicant has not established the critical nature of the dimension where the first gate oxide has a thickness in a range of approximately 300-600A, and wherein the second gate oxide has a thickness in a range of approximately 900-1200A. "The law is replete

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with cases in which the difference between the claimed invention and the prior art is some range or other variable within the claims. . . . In such a situation, the applicant must show that the particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range.” *In re Woodruff*, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990).

Finally, since Merchant and Seeds are both from the same field of endeavor, the purpose disclosed by Seeds would have been recognized in the pertinent art of Merchant.

6. Claim 12 is rejected under 35 U.S.C. 103(a) as obvious over Merchant (U.S. Patent No. 5,412,241) in view of Applicant’s Related Art, Seeds et al. (U.S. Patent No. 3,936,858) and Shirahata et al. (U.S. Publication No. 2002/0175380).

In regards to claim 12, Merchant fails to disclose the following:

a) a thickness of approximately 1200A of the second gate oxide results in an increase from approximately $1e^{12} \text{ cm}^{-2}$ to approximately $2e^{12} \text{ cm}^{-2}$ of a maximum allowable charge, and a decrease of approximately 30% for a specific-on-resistance of the device.

However, Seeds et al. (“Seeds”) discloses a gate oxide that has a thickness around 1200A (For Example: See Column 8 Lines 52-55). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a gate oxide that has a thickness in a range of approximately around 1200A as disclosed in Seeds because it aids in increasing the threshold voltage (For Example: See Column 8 Lines 52-55).

However, Shirahata et al. (“Shirahata”) discloses a gate oxide that has various charges (For Example: See Abstract). It would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device of Merchant to include a

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gate oxide that has a various charges as disclosed in Shirahata because it aids in increasing the threshold voltage.

Additionally, the applicant has not established the critical nature of the dimension where the first gate oxide has a thickness in a range of approximately 300-600A, and wherein the second gate oxide has a thickness in a range of approximately 900-1200A. “The law is replete with cases in which the difference between the claimed invention and the prior art is some range or other variable within the claims. . . . In such a situation, the applicant must show that the particular range is critical, generally by showing that the claimed range achieves unexpected results relative to the prior art range.” *In re Woodruff*, 919 F.2d 1575, 16 USPQ2d 1934 (Fed. Cir. 1990).

Finally, since Merchant, Seeds and Shirahata are both from the same field of endeavor, the purpose disclosed by Seeds and Shirahata would have been recognized in the pertinent art of Merchant.

Conclusion

7. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Monica Lewis whose telephone number is 703-305-3743. If attempts to reach the examiner by telephone are unsuccessful, the examiner’s supervisor, Amir Zarabian can be reached on 703-308-4905. The fax phone number for the organization where this application or proceeding is assigned is 703-308-7722 for regular and after final

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communications. Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

ML

November 7, 2003



AMIR ZARARIAN
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